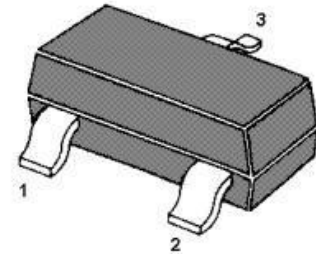


### PNP SILICON EPITAXIAL POWER TRANSISTOR

These devices are intended for use in audio frequency power amplifier and low speed switching applications

**MARKING: B772**



1. BASE
2. EMITTER
3. COLLECTOR

#### Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)

Parameter	Symbol	Value	Unit
Collector Base Voltage	-V <sub>CBO</sub>	40	V
Collector Emitter Voltage	-V <sub>CEO</sub>	30	V
Emitter Base Voltage	-V <sub>EBO</sub>	5	V
Collector Current	-I <sub>C</sub>	3	A
Peak Collector Current (t = 10 ms)	-I <sub>CP</sub>	7	A
Base Current	-I <sub>B</sub>	0.6	A
Total Power Dissipation @ T <sub>a</sub> = 25 °C	P <sub>D</sub>	0.5	W
Total Power Dissipation @ T <sub>c</sub> = 25 °C	P <sub>D</sub>	5	W
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	250	°C/W
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 65 to + 150	°C

#### Characteristics at T<sub>a</sub> = 25 °C

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at -V <sub>CE</sub> = 2 V, -I <sub>C</sub> = 20 mA at -V <sub>CE</sub> = 2 V, -I <sub>C</sub> = 1 A Current Gain Group	R	30	-	-	-
	Q	60	-	120	-
	P	100	-	200	-
	E	160	-	320	-
	E	200	-	400	-
Collector Base Cutoff Current at -V <sub>CB</sub> = 30 V	-I <sub>CBO</sub>	-	-	1	μA
Emitter Base Cutoff Current at -V <sub>EB</sub> = 3 V	-I <sub>EBO</sub>	-	-	1	μA
Collector Base Breakdown Voltage at -I <sub>C</sub> = 1 mA	-V <sub>(BR)CBO</sub>	40	-	-	V
Collector Emitter Breakdown Voltage at -I <sub>C</sub> = 1 mA	-V <sub>(BR)CEO</sub>	30	-	-	V
Emitter Base Breakdown Voltage at -I <sub>E</sub> = 1 mA	-V <sub>(BR)EBO</sub>	5	-	-	V
Collector Emitter Saturation Voltage at -I <sub>C</sub> = 2 A, -I <sub>B</sub> = 200 mA	-V <sub>CE(sat)</sub>	-	-	0.5	V
Base Emitter Saturation Voltage at -I <sub>C</sub> = 2 A, -I <sub>B</sub> = 200 mA	-V <sub>BE(sat)</sub>	-	-	2	V
Current Gain Bandwidth Product at -V <sub>CE</sub> = 5 V, -I <sub>C</sub> = 100 mA,	f <sub>T</sub>	-	80	-	MHz
Output Capacitance at -V <sub>CB</sub> = 10 V, f = 1 MHz	C <sub>ob</sub>	-	55	-	pF

